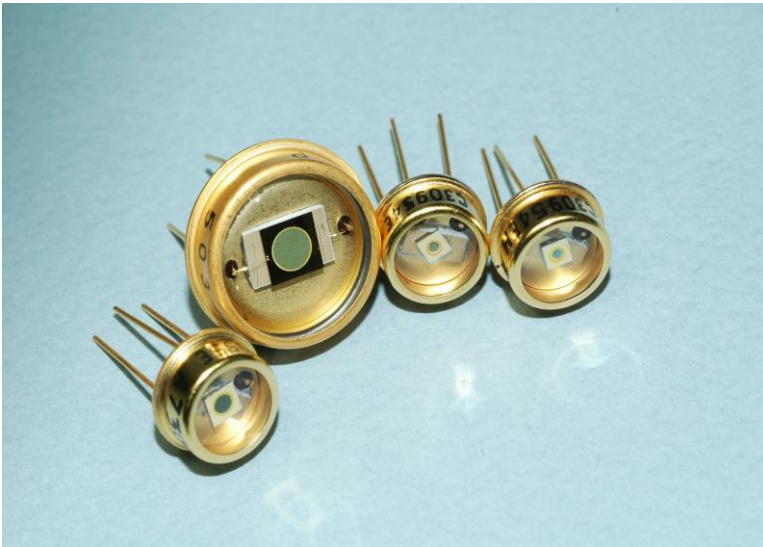


C30954EH, C30955EH and C30956EH Series Long Wavelength Enhanced Silicon Avalanche Photodiodes for range finding, LIDAR, and YAG laser detection



Excelitas' C30954EH, C30955EH, and C30956EH are general purpose silicon avalanche photodiodes made using a double-diffused "reach through" structure. The design of these photodiodes is such that their long wave response (i.e. > 900 nm) has been enhanced without introducing any undesirable properties.

These APDs have quantum efficiency of up to 40% at 1060 nm. At the same time, the diodes retain the low noise, low capacitance, and fast rise and fall times characteristics.

Standard versions of these APDs are available in hermetically-sealed, flat top glass TO-5 packages for the smaller area C30954EH and C30955EH, and a TO-8 package for the larger area C30956EH.

To help simplify many design needs, these Si APDs are also available in Excelitas' high-performance hybrid preamplifier module, C30659 Series, as well as the preamplifier and Thermo-electric (TE) cooler incorporated module, the LLAM Series.

Recognizing that different applications have different performance requirements, Excelitas offers a wide range of customization options for these APDs to meet your design challenges. TE cooler-packaged versions are available on a custom basis. Operating and breakdown voltage selection, dark current and NEP screening, custom device testing and packaging are among the many application-specific solutions available.

Key Features

- High quantum efficiency at 1060 nm
- Fast response time
- Wide operating temperature range
- Low capacitance
- Hermetically-sealed packages
- RoHS-compliant

Applications

- Range finding
- LIDAR
- YAG laser detection

Long Wavelength Enhanced Silicon Avalanche Photodiodes

Table 1. Mechanical and Optical Characteristics

Photosensitive surface	C30954EH	C30955EH	C30956EH	Unit
Shape	Circular	Circular	Circular	
Useful Area	0.5	1.77	7	mm ²
Useful Diameter	0.8	1.5	3	mm
Package	TO-5	TO-5	TO-8	
Field of View α (see figure 10) ¹	110	104	132	Degrees
Field of View α' (see figure 10) ¹	125	130	150	Degrees

1. The values specified for field of view are approximate and are critically dependent on the dimensional tolerances of the packages component parts.

Table 2. Electrical Characteristics at T_A = 22 °C; at the DC reverse operating voltage V_r, supplied with the device²

Parameter	C30954EH			C30955EH			C30956EH			Unit
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
Breakdown Voltage, V _{BR} ²	300	375	475	315	390	490	325	400	500	V
Temperature Coefficient of V _R , for Constant M	-	2.4	-	-	2.4	-	-	2.4	-	V/°C
Gain (M)	-	120	-	-	100	-	-	75	-	
Responsivity @ 900 nm @ 1060 nm @ 1150 nm	65 30 4	75 36 5	- - -	55 26 4	70 34 5	- - -	36 20 2.8	45 25 3.5	- - -	A/W A/W A/W
Quantum Efficiency @ 900 nm @ 1060 nm @ 1150 nm	- - -	85 36 5	- - -	- - -	85 40 5	- - -	- - -	85 40 5	- - -	% % %
Total Dark Current, I _d	-	50	100	-	100	200	-	100	200	nA
Noise Current, i _n <small>f=10kHz, Δf=1.0Hz</small>	-	0.7	2	-	0.7	2	-	0.8	2.2	pA/√Hz
Capacitance, C _d	-	2	4	-	3	5	-	10	12	pF
Series resistance	-	-	15	-	-	15	-	-	15	Ω
Rise & Fall Time, R _L =50 Ω, 10%-90%-10% points	-	2	3	-	2	3.5	-	2	3.5	ns

2. A specific value of V_r is supplied with each device. When the photodiode is operated at this voltage, the device will meet the electrical characteristic limits shown above. The voltage value will be within the range of 275 to 450 volts.

Long Wavelength Enhanced Silicon Avalanche Photodiodes

Table 3 – Maximum ratings

Parameter	Min	Typical	Max	Unit
Reverse Bias Current			200	μA
Photocurrent Density, J_p , at 22 °C: Average value, continuous operation			5	mA/mm ²
Peak value			20	
Forward Current, I_F , at 22°C: Average value, continuous operation			5	mA
Peak value (For 1 second duration, non-repetitive)			50	
Storage Temperature	-60		+100	°C
Operating Temperature	-40		+70	
Soldering, 5 seconds, leads only			260	°C

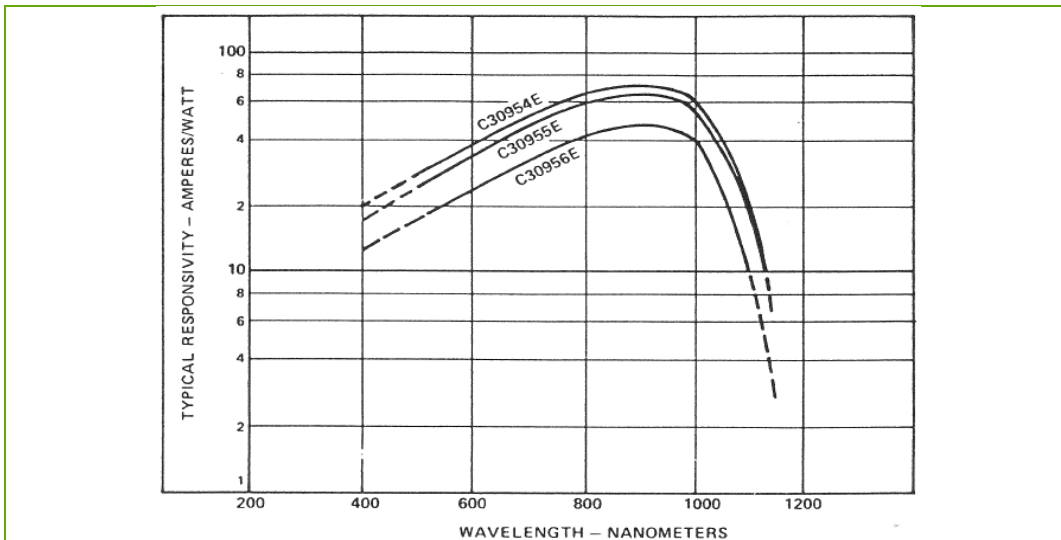


Figure 1
Typical Spectral
Responsivity
Characteristics

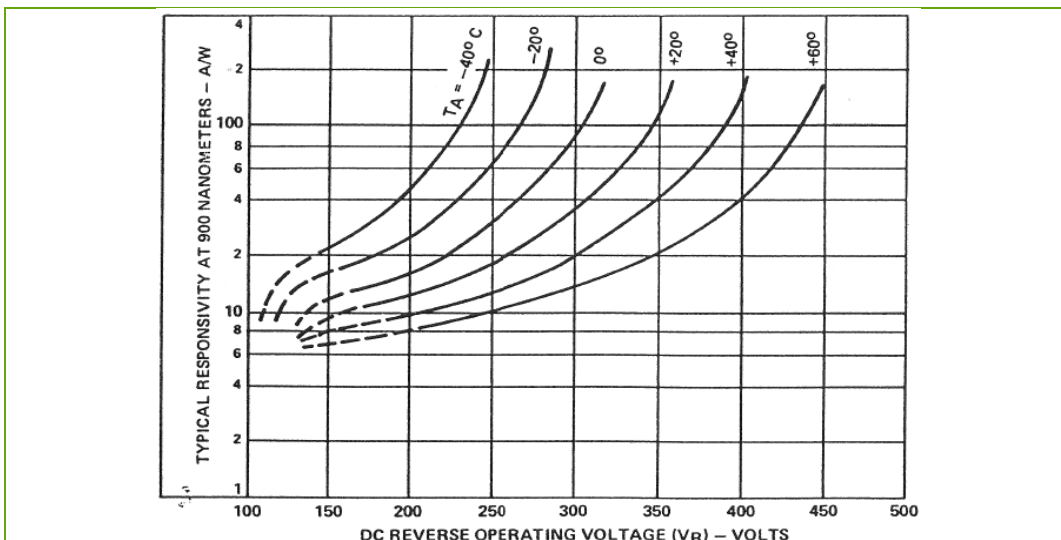


Figure 2
Typical Responsivity at
900 nm vs. Operating
Voltage - C30954EH

Long Wavelength Enhanced Silicon Avalanche Photodiodes

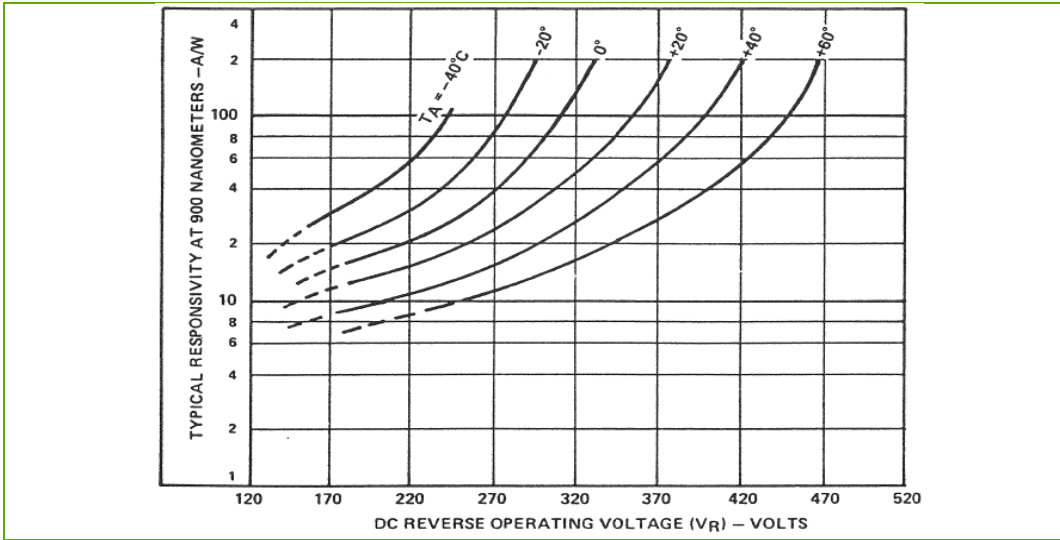


Figure 3
Typical Responsivity at 900 nm vs. Operating Voltage - C30955EH

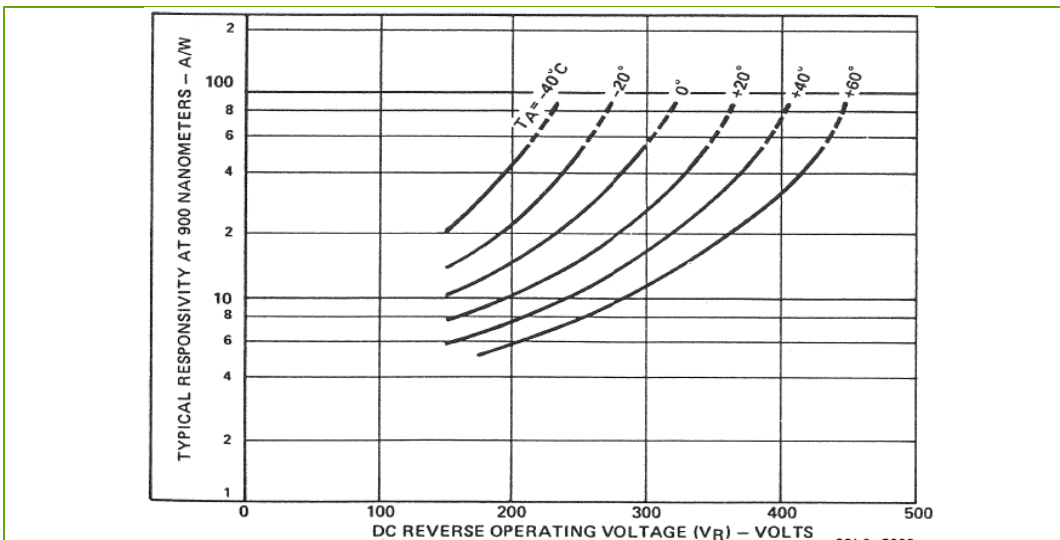


Figure 4
Typical Responsivity at 900 nm vs. Operating Voltage - C30956EH

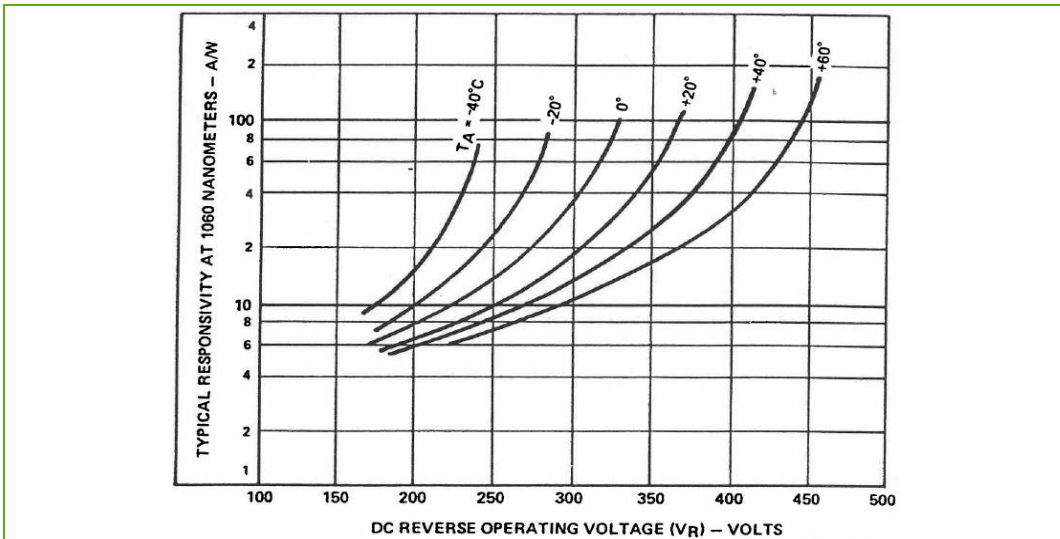


Figure 5
Typical Responsivity at 1060 nm vs. Operating Voltage - C30954EH

Long Wavelength Enhanced Silicon Avalanche Photodiodes

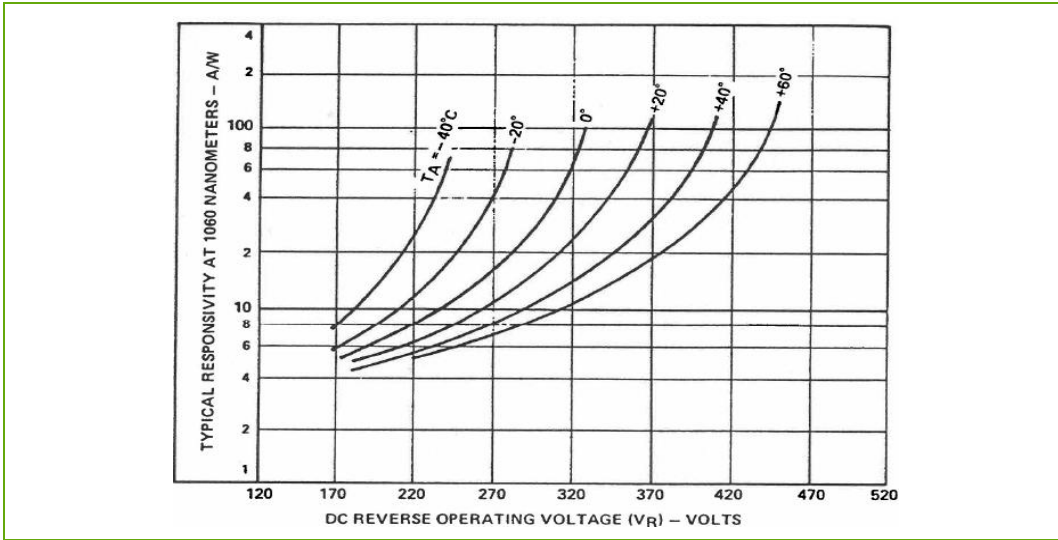


Figure 6
Typical Responsivity at 1060 nm vs. Operating Voltage - C30955EH

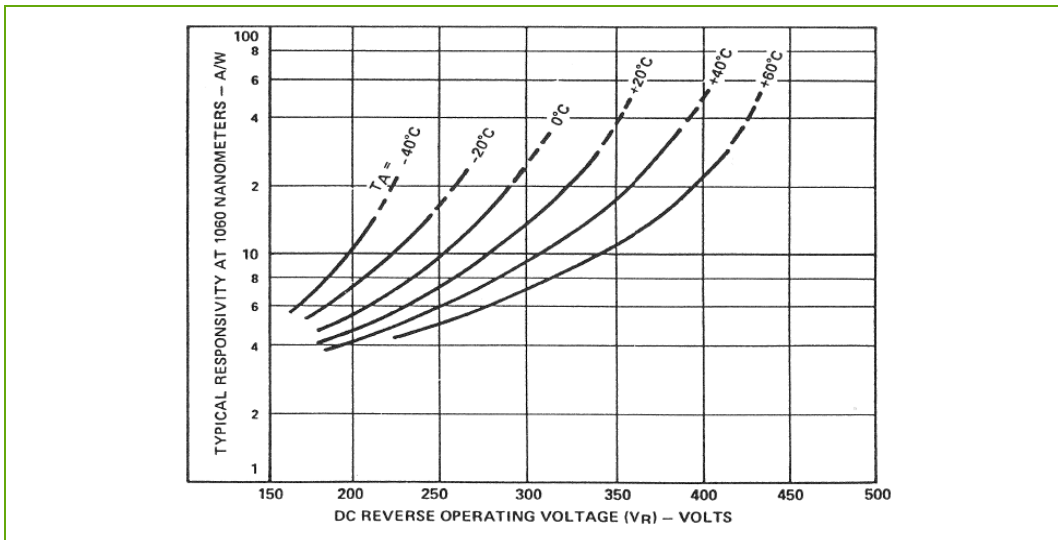


Figure 7
Typical Responsivity at 1060 nm vs. Operating Voltage - C30956EH

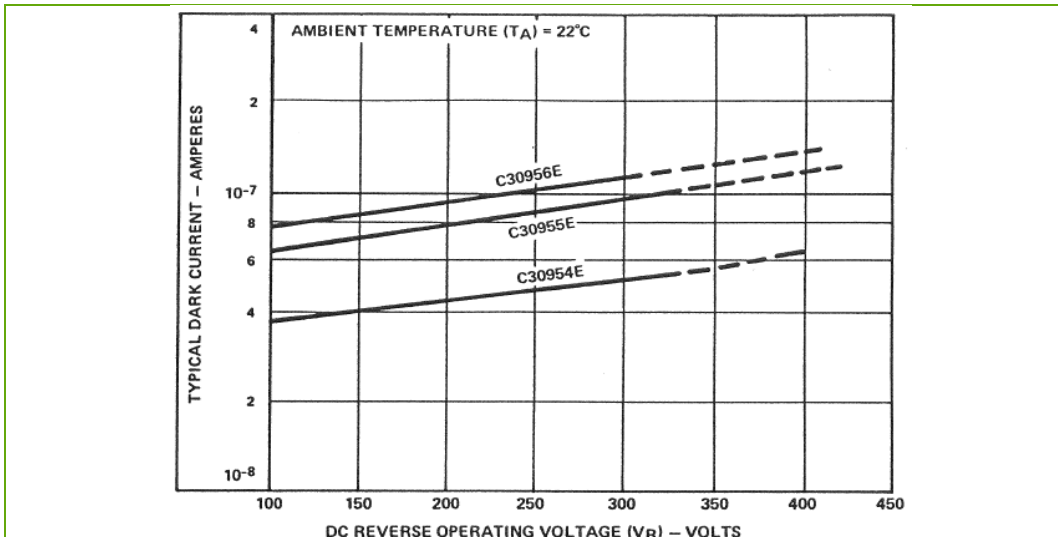


Figure 8
Typical dark current vs. Operating Voltage

Long Wavelength Enhanced Silicon Avalanche Photodiodes

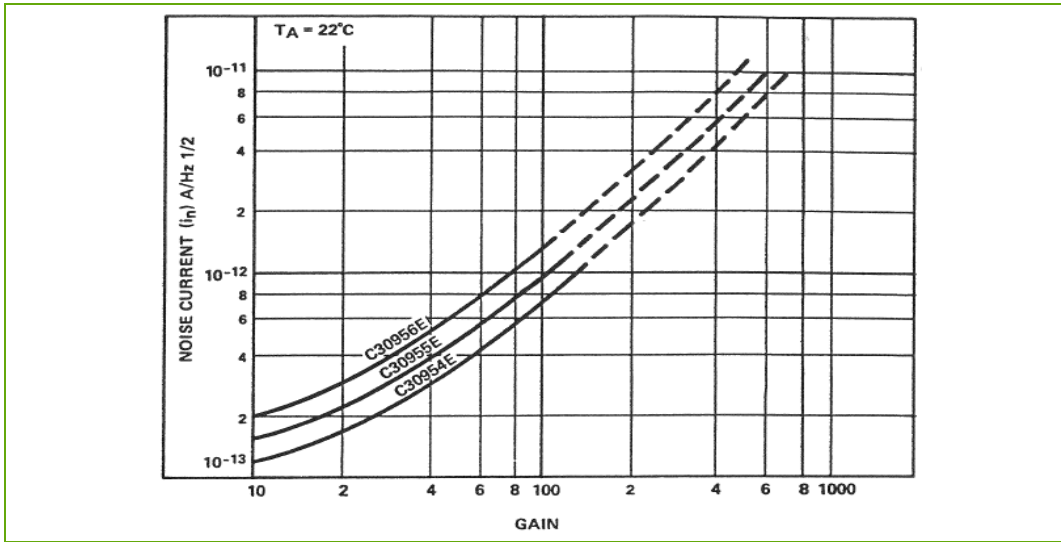


Figure 9
Typical noise current vs. Gain

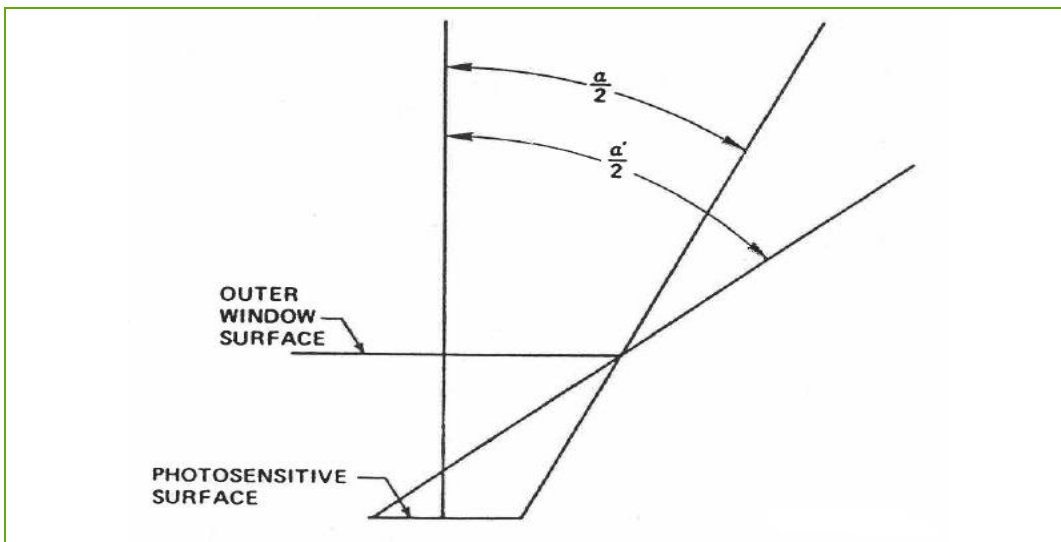


Figure 10
Definition of Half-Angle approximate field of view.

For incident radiation at angles $\leq \alpha/2$, the photosensitive surface is totally illuminated.

For incident radiation at angles $> \alpha/2$, but $\leq \alpha'/2$, the photosensitive surface is partially illuminated.

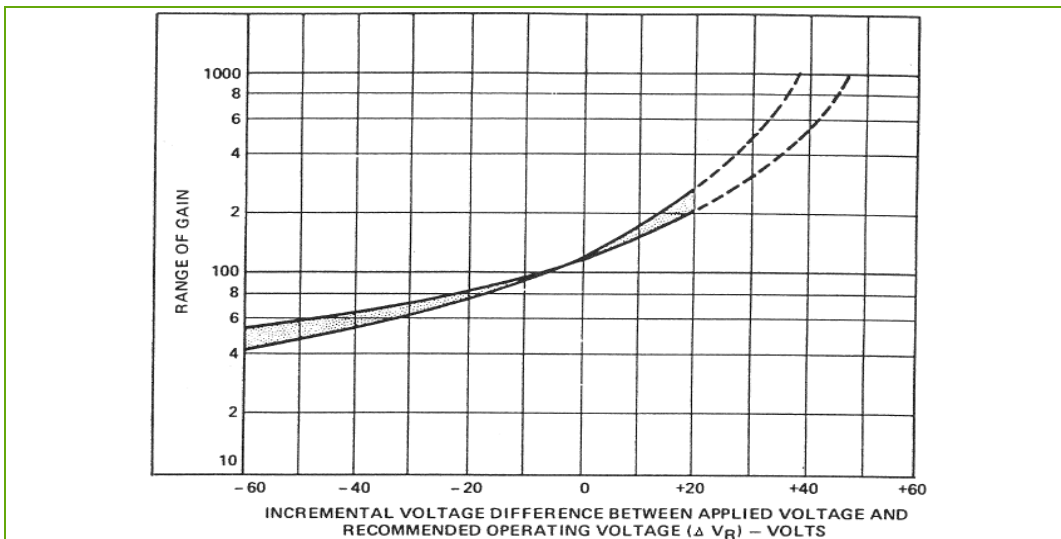


Figure 11
Variation of Gain as a Function of Difference between Actual Applied Operating Voltage and Recommended Operating Voltage - C30954EH

Long Wavelength Enhanced Silicon Avalanche Photodiodes

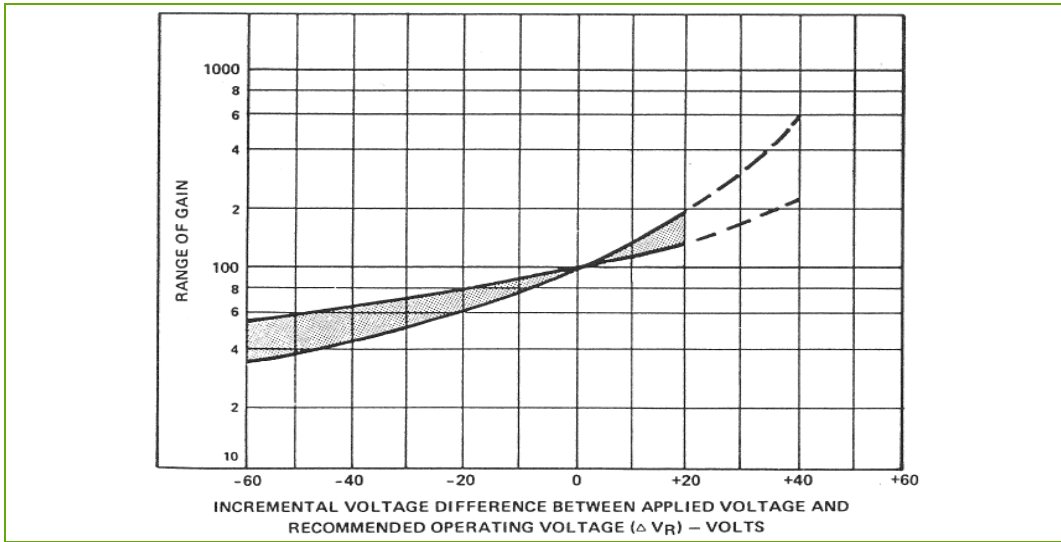


Figure 12
Variation of Gain as a Function of Difference between Actual Applied Operating Voltage and Recommended Operating Voltage - C30955EH

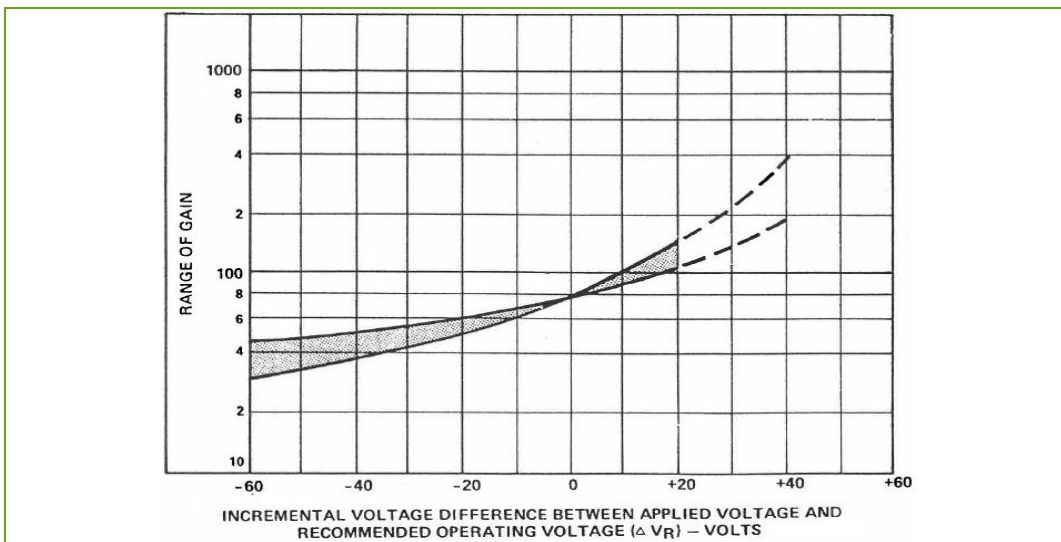


Figure 13
Variation of Gain as a Function of Difference between Actual Applied Operating Voltage and Recommended Operating Voltage - C30956EH

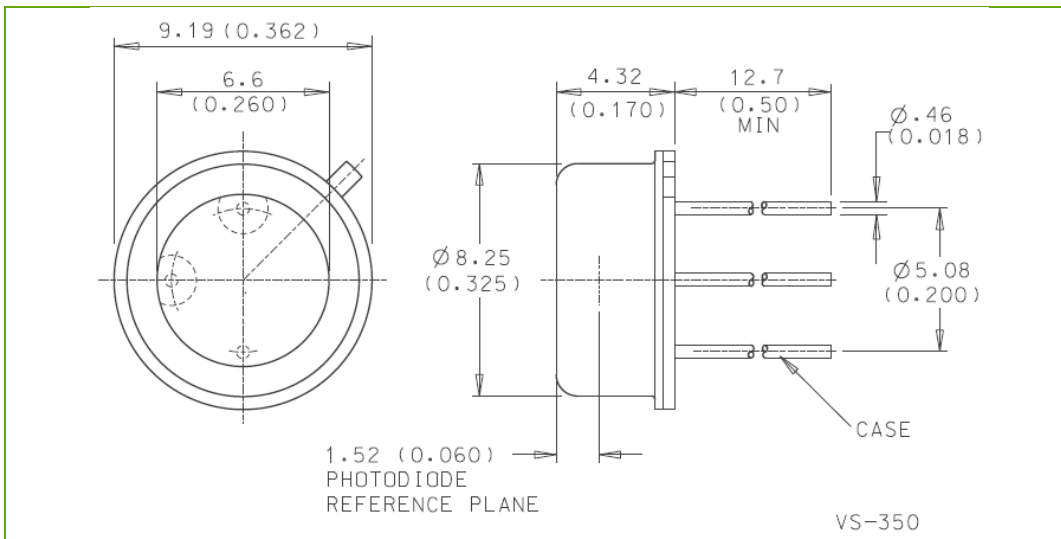


Figure 14
Dimensional Outline
C30954EH, C30955EH
Types

Low-Profile TO-5 Package
dimensions in mm(inch)

